

Akihiro Ohtake

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

90
papers

1,529
citations

20
h-index

34
g-index

93
ext. papers

1,620
ext. citations

3.5
avg, IF

4.66
L-index

#	Paper	IF	Citations
90	Annealing-Induced Structural Evolution of InAs Quantum Dots on InP (111)A Formed by Droplet Epitaxy. <i>Crystal Growth and Design</i> , 2021 , 21, 3947-3953	3.5	1
89	Two-Dimensional WSe ₂ /MoSe ₂ Heterostructures Grown by Molecular-Beam Epitaxy. <i>Journal of Physical Chemistry C</i> , 2021 , 125, 11257-11261	3.8	3
88	Polarization Anisotropies in Strain-Free, Asymmetric, and Symmetric Quantum Dots Grown by Droplet Epitaxy. <i>Nanomaterials</i> , 2021 , 11,	5.4	1
87	Strain relaxation in InAs heteroepitaxy on lattice-mismatched substrates. <i>Scientific Reports</i> , 2020 , 10, 4606	4.9	15
86	Effect of Substrate Orientation on MoSe ₂ /GaAs Heteroepitaxy. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 5196-5203	3.8	8
85	Heteroepitaxy of MoSe ₂ on Si(111) substrates: Role of surface passivation. <i>Applied Physics Letters</i> , 2019 , 114, 053106	3.4	5
84	Atomic structure and passivated nature of the Se-treated GaAs(111)B surface. <i>Scientific Reports</i> , 2018 , 8, 1220	4.9	9
83	Strain Relaxation in GaSb/GaAs(111)A Heteroepitaxy Using Thin InAs Interlayers. <i>ACS Omega</i> , 2018 , 3, 15592-15597	3.9	2
82	Evolution of Surface and Interface Structures in Molecular-Beam Epitaxy of MoSe ₂ on GaAs(111)A and (111)B. <i>Crystal Growth and Design</i> , 2017 , 17, 363-367	3.5	7
81	First-principles study of locally disordered structures of Mn-induced GaAs(001)-(2 × 2) surface. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 08NB21	1.4	
80	Growth of Metamorphic InGaAs on GaAs (111)A: Counteracting Lattice Mismatch by Inserting a Thin InAs Interlayer. <i>Crystal Growth and Design</i> , 2016 , 16, 5412-5417	3.5	11
79	Mn-Induced Surface Reconstructions on GaAs(001). <i>Journal of Physical Chemistry C</i> , 2016 , 120, 6050-6063	3.8	2
78	Overcoming metal-induced fluorescence quenching on plasmophotonic metasurfaces coated by a self-assembled monolayer. <i>Chemical Communications</i> , 2015 , 51, 11470-3	5.8	28
77	Droplet epitaxy growth of telecom InAs quantum dots on metamorphic InAlAs/GaAs(111)A. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DH07	1.4	8
76	Size-dependent line broadening in the emission spectra of single GaAs quantum dots: Impact of surface charge on spectral diffusion. <i>Physical Review B</i> , 2015 , 92,	3.3	29
75	Extremely High- and Low-Density of Ga Droplets on GaAs{111}A,B: Surface-Polarity Dependence. <i>Crystal Growth and Design</i> , 2015 , 15, 485-488	3.5	13
74	Heteroepitaxy of GaSb on Si(111) and fabrication of HfO ₂ /GaSb metal-oxide-semiconductor capacitors. <i>Applied Physics Letters</i> , 2014 , 104, 032101	3.4	8

73	Self-Assembled Growth of Ga Droplets on GaAs(001): Role of Surface Reconstructions. <i>Crystal Growth and Design</i> , 2014 , 14, 3110-3115	3.5	8
72	Electrical characteristics and thermal stability of HfO ₂ metal-oxide-semiconductor capacitors fabricated on clean reconstructed GaSb surfaces. <i>Applied Physics Letters</i> , 2014 , 104, 232104	3.4	19
71	Controlled incorporation of Mn in GaAs: Role of surface reconstructions. <i>Physical Review B</i> , 2013 , 87,	3.3	11
70	As-rich (2 \times) surface reconstruction on GaAs(111)A. <i>Surface Science</i> , 2012 , 606, 1864-1870	1.8	7
69	Cation-anion mixed-dimer structure of Al-induced (2 \times) reconstruction on InAs(001). <i>Surface Science</i> , 2012 , 606, 1886-1891	1.8	
68	Controlling Anion Composition at Metal/Insulator/Semiconductor Interfaces on III/V Channels by Plasma Processing. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 065701	1.4	2
67	Impact of Cation Surface Termination on the Electrical Characteristics of HfO ₂ /InGaAs(001) Metal/Oxide/Semiconductor Capacitors. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 10PD01	1.4	2
66	Polarity controlled InAs{111} films grown on Si(111). <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 031804	1.3	15
65	Atomic-scale characterization of the N incorporation on GaAs(001). <i>Journal of Applied Physics</i> , 2011 , 110, 033506	2.5	5
64	Impact of Cation Surface Termination on the Electrical Characteristics of HfO ₂ /InGaAs(001) Metal/Oxide/Semiconductor Capacitors. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 10PD01	1.4	2
63	Self-Assembly of Symmetric GaAs Quantum Dots on (111)A Substrates: Suppression of Fine-Structure Splitting. <i>Applied Physics Express</i> , 2010 , 3, 065203	2.4	73
62	Effect of Interface Oxidation on the Electrical Characteristics of HfO ₂ /Ultrathin-Epitaxial-Ge/GaAs(100) Structures. <i>Applied Physics Express</i> , 2010 , 3, 035701	2.4	2
61	Variable stoichiometry in Sb-induced (2 \times) reconstructions on GaAs(001). <i>Physical Review B</i> , 2009 , 80,	3.3	4
60	Relationships between Interface Structures and Electrical Properties in the High-k/III/V System. <i>Materials Research Society Symposia Proceedings</i> , 2009 , 1194, 68		2
59	Anisotropic kinetics on growing Ge(001) surfaces. <i>Surface Science</i> , 2009 , 603, 826-830	1.8	6
58	Ge-induced (1 \times) surface reconstruction on GaAs(001): A precursor to As segregation. <i>Physical Review B</i> , 2008 , 77,	3.3	2
57	Influence of initial surface reconstruction on the interface structure of HfO ₂ /GaAs. <i>Applied Surface Science</i> , 2008 , 254, 7565-7568	6.7	15
56	Surface reconstructions on GaAs(001). <i>Surface Science Reports</i> , 2008 , 63, 295-327	12.9	135

55	Structure and composition of Ga-rich ($6\bar{6}$) reconstructions on GaAs(001). <i>Physical Review B</i> , 2007 , 75,	3.3	14
54	Ga-rich GaAs(001) surface from ab initio calculations: Atomic structure of the ($4\bar{6}$) and ($6\bar{6}$) reconstructions. <i>Physical Review B</i> , 2006 , 73,	3.3	18
53	Structures of the As-deficient phase on GaAs(001)($2\bar{4}$). <i>Physical Review B</i> , 2006 , 74,	3.3	14
52	Self-assembled growth of ordered GaAs nanostructures. <i>Applied Physics Letters</i> , 2006 , 89, 083108	3.4	10
51	Atomic structure of the Ga nanoclusters on Si(111)($7\bar{7}$). <i>Physical Review B</i> , 2006 , 73,	3.3	18
50	Proposal of Selective Growth Technique Using Periodic Strain Field Caused by Misfit Dislocations. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, L1422-L1424	1.4	3
49	Ga-rich limit of surface reconstructions on GaAs(001): atomic structure of the (4×6) phase. <i>Physical Review Letters</i> , 2004 , 93, 266101	7.4	51
48	Structural features of Ga-rich GaAs(001) surfaces: Scanning tunneling microscopy study. <i>Physical Review B</i> , 2004 , 70,	3.3	21
47	Kinetics in surface reconstructions on GaAs(001). <i>Physical Review Letters</i> , 2004 , 92, 236105	7.4	71
46	GaAs dimer structure for the GaAs(001)-c($4\bar{4}$) surface. <i>Surface Science</i> , 2004 , 566-568, 58-62	1.8	10
45	RHEED Studies of GaAs Surface Structure. <i>Hyomen Kagaku</i> , 2003 , 24, 136-144		
44	Two types of structures for the GaAs(001)-c($4\bar{4}$) surface. <i>Applied Physics Letters</i> , 2003 , 83, 5193-5195	3.4	50
43	Ga-rich GaAs(0 0 1) surfaces observed by STM during high-temperature annealing in MBE. <i>Journal of Crystal Growth</i> , 2003 , 251, 46-50	1.6	16
42	Structure of Ga-stabilized GaAs(0 0 1) surfaces at high temperatures. <i>Applied Surface Science</i> , 2003 , 212-213, 146-150	6.7	5
41	Gallium-rich reconstructions on GaAs(001). <i>Physica Status Solidi (B): Basic Research</i> , 2003 , 240, 91-98	1.3	25
40	Large anisotropy in thermal atomic vibrations at the InSb(111)A($2\bar{2}$) surface. <i>Physical Review B</i> , 2003 , 68,	3.3	2
39	Strain-induced surface segregation in In _{0.5} Ga _{0.5} As/GaAs heteroepitaxy. <i>Applied Physics Letters</i> , 2002 , 80, 3931-3933	3.4	6
38	Structure analysis of the Ga-stabilized GaAs(001) $\bar{4}$ ($8\bar{4}$) surface at high temperatures. <i>Physical Review B</i> , 2002 , 65,	3.3	27

37	Growth mode of In _x Ga _{1-x} As (0. <i>Physical Review B</i> , 2002 , 65,	3.3	8
36	New structure model for the GaAs(001)-c(4x4) surface. <i>Physical Review Letters</i> , 2002 , 89, 206102	7.4	106
35	Indium supply from triisopropylindium onto a GaAs(001) surface at room temperature. <i>Applied Physics Letters</i> , 2002 , 81, 4058-4060	3.4	1
34	Atomic structure of the GaAs(001)($\sqrt{3}\times\sqrt{3}$) surface under As flux. <i>Physical Review B</i> , 2002 , 65,	3.3	53
33	Wurtzite-zinc-blende polytypism in ZnSe on GaAs(111)A. <i>Physical Review B</i> , 2001 , 63,	3.3	10
32	In situ observation of surface processes in InAs/GaAs(001) heteroepitaxy: The role of As on the growth mode. <i>Applied Physics Letters</i> , 2001 , 78, 431-433	3.4	29
31	Surface structures of GaAs{111}A,B($\sqrt{3}\times\sqrt{3}$). <i>Physical Review B</i> , 2001 , 64,	3.3	69
30	Adsorption processes of Se on the GaAs(111)A($\sqrt{2}\times\sqrt{2}$) surface. <i>Applied Surface Science</i> , 2000 , 162-163, 419-424	6.7	2
29	Strain relaxation in InAs/GaAs(111)A heteroepitaxy. <i>Physical Review Letters</i> , 2000 , 84, 4665-8	7.4	41
28	Structure and composition of the ZnSe(001) surface during atomic-layer epitaxy. <i>Physical Review B</i> , 1999 , 60, 8326-8332	3.3	34
27	In situ observation of strain-induced optical anisotropy of Zn _{Sx} Se _{1-x} /GaAs(110) during molecular-beam epitaxy. <i>Physical Review B</i> , 1999 , 60, 8909-8914	3.3	8
26	Real-time analysis of adsorption processes of Zn on the GaAs(001)($\sqrt{3}\times\sqrt{3}$) surface. <i>Physical Review B</i> , 1999 , 60, 8713-8718	3.3	17
25	X-ray reflectivity from ZnSe/GaAs heterostructures. <i>Journal of Applied Physics</i> , 1999 , 85, 1520-1523	2.5	10
24	Adsorption of Zn on the GaAs(001)-($\sqrt{3}\times\sqrt{3}$) surface. <i>Applied Physics Letters</i> , 1999 , 74, 2975-2977	3.4	9
23	Self-assembled formation of ZnCdSe quantum dots on atomically smooth ZnSe surfaces on GaAs(001) by molecular beam epitaxy. <i>Thin Solid Films</i> , 1999 , 357, 1-7	2.2	10
22	Atomic layer epitaxy processes of ZnSe on GaAs(0 0 1) as observed by beam-rocking reflection high-energy electron diffraction (RHEED) and total-reflection-angle X-ray spectroscopy (TRAXS). <i>Journal of Crystal Growth</i> , 1999 , 201-202, 490-493	1.6	6
21	Structure of Se-adsorbed GaAs(111)A-($\sqrt{3}\times\sqrt{3}$)-R30° surface. <i>Physical Review B</i> , 1999 , 59, 8032-8036	3.3	16
20	Atomic nitrogen doping in p-ZnSe with high activation ratio using a high-power plasma source. <i>Journal of Crystal Growth</i> , 1998 , 184-185, 411-414	1.6	7

19	Characterization and control of II \bar{V} /III \bar{V} heterovalent interfaces. <i>Journal of Crystal Growth</i> , 1998 , 184-185, 163-172	1.6	26
18	Polar surface dependence of epitaxy processes: ZnSe on GaAs{111}A, B-(2 $\bar{0}$). <i>Applied Surface Science</i> , 1998 , 130-132, 398-402	6.7	4
17	Reflection high-energy electron diffraction analysis of the InSb{111}A,B-(2 $\bar{0}$) surfaces. <i>Surface Science</i> , 1998 , 396, 394-399	1.8	16
16	In situ determination of in-plane strain anisotropy in ZnSe(001)/GaAs layers using reflectance difference spectroscopy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 2342		13
15	The role of zinc pre-exposure in low-defect ZnSe growth on As-stabilized GaAs (001). <i>Applied Physics Letters</i> , 1998 , 73, 939-941	3.4	22
14	Defect generation in layer-by-layer-grown ZnSe films on Te-terminated GaAs(001) surfaces. <i>Physical Review B</i> , 1998 , 57, 1410-1413	3.3	9
13	Non-Contact and Non-Destructive Measurement of Carrier Concentration of Nitrogen-Doped ZnSe by Reflectance Difference Spectroscopy. <i>Japanese Journal of Applied Physics</i> , 1997 , 36, 6638-6644	1.4	14
12	Growth mode and defect generation in ZnSe heteroepitaxy on Te-terminated GaAs(001) surfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 1254		9
11	Reflectance-difference studies of interface-formation and initial-growth processes in ZnSe/GaAs(001) heteroepitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 1212		8
10	Atomic nitrogen doping in p-ZnSe molecular beam epitaxial growth with almost 100% activation ratio. <i>Applied Physics Letters</i> , 1997 , 71, 1077-1079	3.4	9
9	Nature and origins of stacking faults from a ZnSe/GaAs interface. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997 , 15, 1241		29
8	Surface processes during heteroepitaxy of ZnSe on GaAs(111)A as observed by reflection high-energy electron diffraction. <i>Physical Review B</i> , 1997 , 56, 14909-14912	3.3	11
7	ZnSe epitaxy on a GaAs(110) surface. <i>Applied Physics Letters</i> , 1997 , 71, 1192-1194	3.4	10
6	Initial growth processes of Ag on polar and non-polar semiconductor substrates. <i>Surface Science</i> , 1997 , 380, L437-L440	1.8	2
5	Molecular beam epitaxial growth of P-ZnSe:N using a novel plasma source. <i>Journal of Electronic Materials</i> , 1997 , 26, 705-709	1.9	1
4	Dependence of defect generation and structure on interface chemistry in ZnSe/GaAs. <i>Applied Surface Science</i> , 1997 , 117-118, 495-502	6.7	10
3	Heterovalent ZnSe/GaAs Interfaces. <i>Physica Status Solidi (B): Basic Research</i> , 1997 , 202, 657-668	1.3	3
2	Geometry and lattice formation of surface layers of Sn growing on InSb{111}A,B. <i>Physical Review B</i> , 1996 , 54, 10358-10361	3.3	10

- 1 Surface phase transition and interface interaction in the alpha -Sn/InSb{111} system. *Physical Review B*, **1994**, 50, 7567-7572 33 55